# XP0111M

### Silicon PNP epitaxial planar type

For switching/digital circuits

#### Features

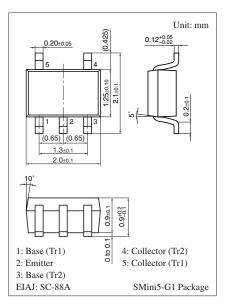
- Two elements incorporated into one package (Emitter-coupled transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

#### Basic Part Number

• UNR211M (UN211M) × 2

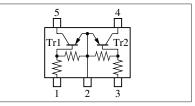
$\mathbf{I}_{a} = 25 \text{ C}$							
Symbol	Rating	Unit					
V <sub>CBO</sub>	-50	V					
V <sub>CEO</sub>	-50	V					
I <sub>C</sub>	-100	mA					
P <sub>T</sub>	150	mW					
Tj	150	°C					
T <sub>stg</sub>	-55 to +150	°C					
	Symbol V <sub>CBO</sub> V <sub>CEO</sub> I <sub>C</sub> P <sub>T</sub> T <sub>j</sub>	$\begin{tabular}{ c c c } \hline Symbol & Rating \\ \hline V_{CBO} & -50 \\ \hline V_{CEO} & -50 \\ \hline I_C & -100 \\ \hline P_T & 150 \\ \hline T_j & 150 \\ \hline \end{tabular}$					





#### Marking Symbol: EK

#### Internal Connection



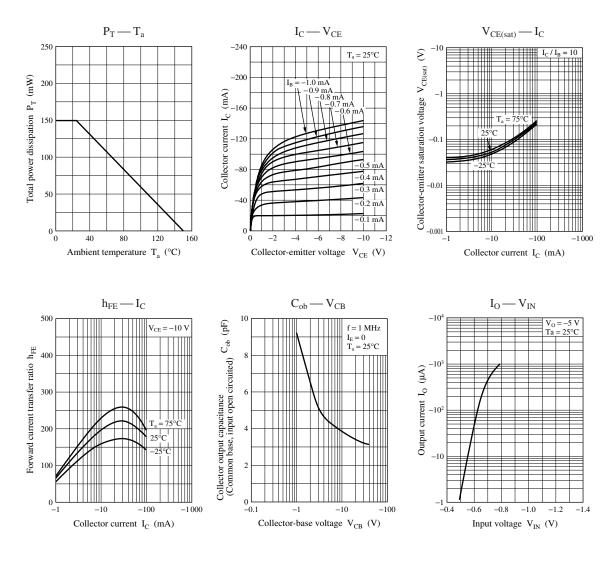
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{C} = -10 \ \mu A, \ I_{E} = 0$	-50			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = -50 \text{ V}, I_E = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = -50 \text{ V}, I_B = 0$			- 0.5	μΑ
Emitter-base cutoff current (Collector open)	I <sub>EBO</sub>	$V_{EB} = -6 V, I_C = 0$			- 0.2	mA
Forward current transfer ratio	h <sub>FE</sub>	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	80			_
h <sub>FE</sub> Ratio *	h <sub>FE(Small</sub>	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	0.50	0.99		
	/Large)					
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = -10 \text{ mA}, I_B = -0.3 \text{ mA}$			- 0.25	V
Output voltage high-level	V <sub>OH</sub>	$V_{CC} = -5 \text{ V}, V_B = -0.5 \text{ V}, R_L = 1 \text{ k}\Omega$	-4.9			V
Output voltage low-level	V <sub>OL</sub>	$V_{CC} = -5 \text{ V},  \text{V}_{\text{B}} = -2.5  \text{V},  \text{R}_{\text{L}} = 1  \text{k}\Omega$			- 0.2	V
Input resistance	R <sub>1</sub>		-30%	2.2	+30%	kΩ
Resistance ratio	R <sub>1</sub> / R <sub>2</sub>			0.047		
Transition frequency	f <sub>T</sub>	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz

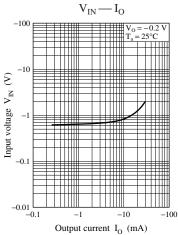
#### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. 2. \*: Ratio between 2 elements

#### XP0111M







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